

LL46

SCHOTTKY BARRIER DIODE

FEATURES :

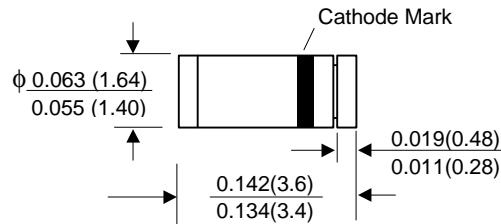
- For general purpose applications.
- This diode features very low turn-on voltage and fast switching. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in the DO-35 case with type designation BAT46

MECHANICAL DATA :

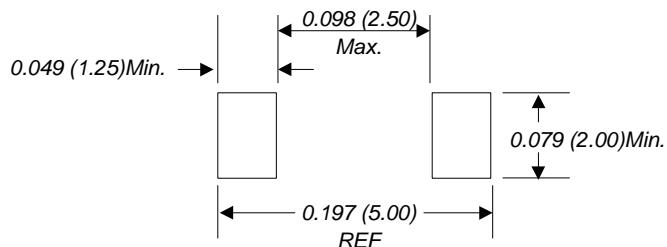
Case: MiniMELF Glass Case (SOD-80C)

Weight: approx. 0.05g

MiniMELF (SOD-80C)



Mounting Pad Layout



Dimensions in inches and (millimeters)

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	150 ⁽¹⁾	mA
Repetitive Peak Forward Current at $t_p < 1s$,	I_{FRM}	350 ⁽¹⁾	mA
Forward Surge Current at $t_p < 10 ms$,	I_{FSM}	750 ⁽¹⁾	mA
Power Dissipation , $T_a = 65 ^\circ C$	P_D	200 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	0.3 ⁽¹⁾	°C/mW
Junction Temperature	T_J	125	°C
Ambient Operating Temperature Range	T_a	-65 to + 125	°C
Storage temperature range	T_s	-65 to + 150	°C

Note: (1) Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics ($T_J = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100 \mu A$ pulses	100	-	-	V
Reverse Current		$V_R = 10 V$	-	-	0.8	
Pulse Test $t_p < 300\mu s$, $\delta < 2\%$	I_R	$V_R = 50 V$	-	-	2.0	μA
		$V_R = 75 V$	-	-	5.0	
Forward Voltage		$I_F = 10mA$	-	-	0.45	V
Pulse Test $t_p < 300\mu s$, $\delta < 2\%$	V_F	$I_F = 250mA$	-	-	1.00	
Diode Capacitance	C_d	$V_R = 1V$, $f = 1MHz$	-	6	-	pF